



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



Micron Serial NOR Flash Memory

3V, Multiple I/O, 4KB, 32KB, 64KB Sector Erase

MT25QL01G BBB

Features

- Stacked device (two 512Mb die)
- SPI-compatible serial bus interface
- Single and double transfer rate (STR/DTR)
- Clock frequency
 - 133 MHz (MAX) for all protocols in STR
 - 90 MHz (MAX) for all protocols in DTR
- Dual/quad I/O commands for increased throughput up to 90 MB/s
- Supported protocols in both STR and DTR
 - Extended I/O protocol
 - Dual I/O protocol
 - Quad I/O protocol
- Execute-in-place (XIP)
- PROGRAM/ERASE SUSPEND operations
- Volatile and nonvolatile configuration settings
- Software reset
- Additional reset pin for selected part numbers
- 3-byte and 4-byte address modes – enable memory access beyond 128Mb
- Dedicated 64-byte OTP area outside main memory
 - Readable and user-lockable
 - Permanent lock with PROGRAM OTP command
- Erase capability
 - Die Erase
 - Sector erase 64KB uniform granularity
 - Subsector erase 4KB, 32KB granularity
- Security and write protection
 - Volatile and nonvolatile locking and software write protection for each 64KB sector
 - Nonvolatile configuration locking
 - Password protection
 - Hardware write protection: nonvolatile bits (BP[3:0] and TB) define protected area size
 - Program/erase protection during power-up
 - CRC detects accidental changes to raw data
- Electronic signature
 - JEDEC-standard 3-byte signature (BA21h)
 - Extended device ID: two additional bytes identify device factory options
- JESD47H-compliant
 - Minimum 100,000 ERASE cycles per sector
 - Data retention: 20 years (TYP)

Options

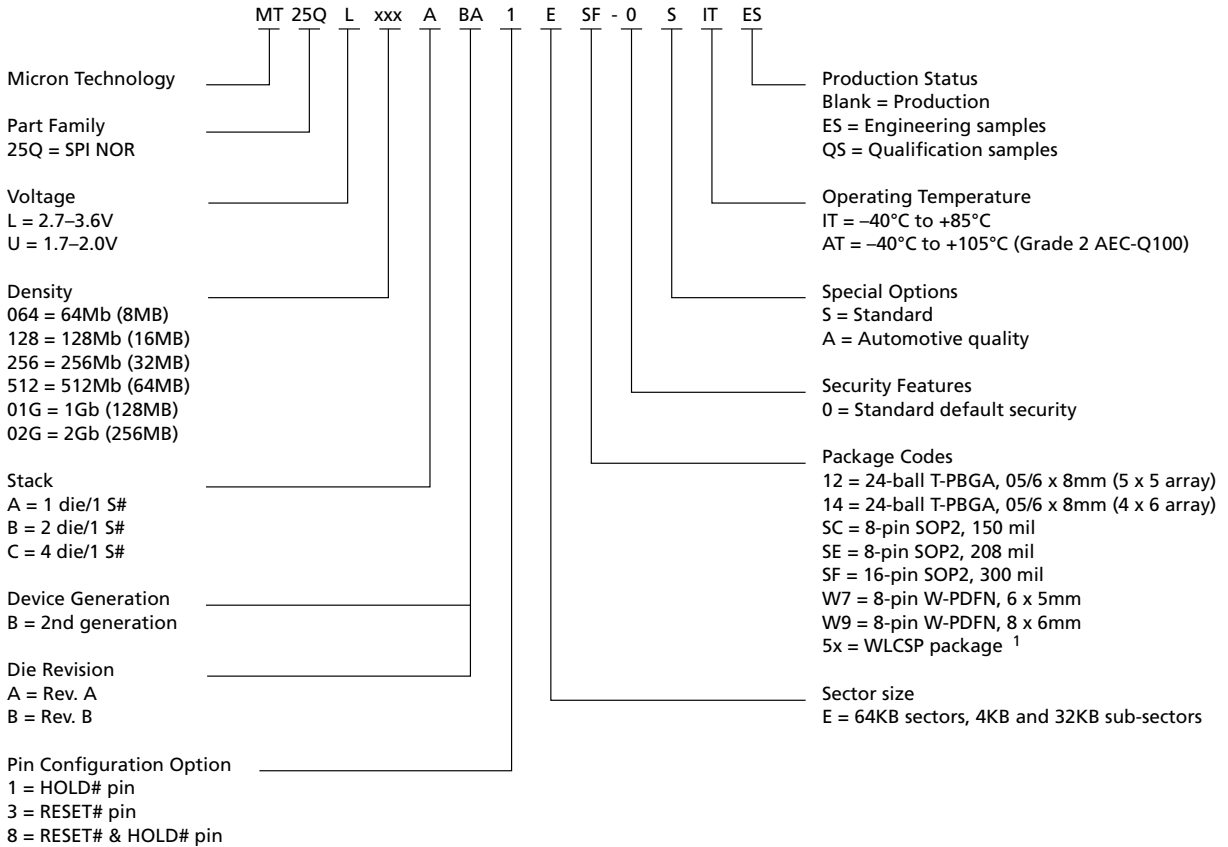
- Voltage
 - 2.7–3.6V
- Density
 - 1Gb
- Device stacking
 - 2 die stacked
- Device generation
 - B
- Die revision
 - B
- Pin configuration
 - HOLD# 1
 - RESET and HOLD# 8
- Sector Size
 - 64KB E
- Packages – JEDEC-standard, RoHS-compliant
 - 24-ball T-PBGA 05/6mm x 8mm (TBGA24) 12
 - 16-pin SOP2, 300 mils (SO16W, SO16-Wide, SOIC-16) SF
 - W-PDFN-8 8mm x 6mm (MLP8 8mm x 6mm) W9
- Standard security
 - 0
- Special options
 - Standard S
 - Automotive A
- Operating temperature range
 - From –40°C to +85°C IT
 - From –40°C to +105°C AT

Marking

Part Number Ordering

Micron Serial NOR Flash devices are available in different configurations and densities. Verify valid part numbers by using Micron’s part catalog search at www.micron.com. To compare features and specifications by device type, visit www.micron.com/products. Contact the factory for devices not found.

Figure 1: Part Number Ordering Information



Note: 1. WLCSP package codes, package size, and availability are density-specific. Contact the factory for availability.



Contents

Device Description	7
Device Logic Diagram	8
Advanced Security Protection	8
Signal Assignments – Package Code: 12	9
Signal Assignments – Package Code: SF	10
Signal Assignments – Package Code: W9	10
Signal Descriptions	11
Package Dimensions – Package Code: 12	12
Package Dimensions – Package Code: SF	13
Package Dimensions – Package Code: W9	14
Memory Map – 1Gb Density	15
Status Register	16
Block Protection Settings	17
Flag Status Register	18
Extended Address Register	19
Internal Configuration Register	20
Nonvolatile Configuration Register	21
Volatile Configuration Register	23
Supported Clock Frequencies	24
Enhanced Volatile Configuration Register	26
Security Registers	27
Sector Protection Security Register	28
Nonvolatile and Volatile Sector Lock Bits Security	29
Volatile Lock Bit Security Register	29
Device ID Data	30
Serial Flash Discovery Parameter Data	31
Command Definitions	32
Software RESET Operations	38
RESET ENABLE and RESET MEMORY Commands	38
READ ID Operations	39
READ ID and MULTIPLE I/O READ ID Commands	39
READ SERIAL FLASH DISCOVERY PARAMETER Operation	40
READ SERIAL FLASH DISCOVERY PARAMETER Command	40
READ MEMORY Operations	41
4-BYTE READ MEMORY Operations	42
READ MEMORY Operations Timings	43
WRITE ENABLE/DISABLE Operations	50
READ REGISTER Operations	51
WRITE REGISTER Operations	53
CLEAR FLAG STATUS REGISTER Operation	55
PROGRAM Operations	56
4-BYTE PROGRAM Operations	57
PROGRAM Operations Timings	57
ERASE Operations	60
SUSPEND/RESUME Operations	62
PROGRAM/ERASE SUSPEND Operations	62
PROGRAM/ERASE RESUME Operations	62
ONE-TIME PROGRAMMABLE Operations	64
READ OTP ARRAY Command	64
PROGRAM OTP ARRAY Command	64



1Gb, 3V Multiple I/O Serial Flash Memory Features

ADDRESS MODE Operations	66
QUAD PROTOCOL Operations	66
ENTER or RESET QUAD INPUT/OUTPUT MODE Command	66
CYCLIC REDUNDANCY CHECK Operations	67
Cyclic Redundancy Check (CRC)	67
State Table	69
XIP Mode	70
Activate or Terminate XIP Using Volatile Configuration Register	70
Activate or Terminate XIP Using Nonvolatile Configuration Register	70
Confirmation Bit Settings Required to Activate or Terminate XIP	71
Terminating XIP After a Controller and Memory Reset	71
Power-Up and Power-Down	72
Power-Up and Power-Down Requirements	72
Power Loss and Interface Rescue	74
Recovery	74
Power Loss Recovery	74
Interface Rescue	74
Initial delivery status	75
Absolute Ratings and Operating Conditions	76
DC Characteristics and Operating Conditions	78
AC Characteristics and Operating Conditions	80
AC Reset Specifications	82
Program/Erase Specifications	85
Revision History	86
Rev. D - 06/16	86
Rev. C - 04/16	86
Rev. B - 9/15	86
Rev. A - 08/15	86

List of Figures

Figure 1: Part Number Ordering Information	2
Figure 2: Block Diagram	7
Figure 3: Logic Diagram	8
Figure 4: 24-Ball T-BGA, 5 x 5 (Balls Down)	9
Figure 5: 16-Pin, Plastic Small Outline – SO16 (Top View)	10
Figure 6: 8-Pin, W-PDFN (Top View)	10
Figure 7: 24-Ball T-PBGA (5 x 5 ball grid array) – 6mm x 8mm	12
Figure 8: 16-Pin SOP2 – 300 mils Body Width	13
Figure 9: W-PDFN-8 (MLP8) – 8mm x 6mm	14
Figure 10: Internal Configuration Register	20
Figure 11: Sector and Password Protection	27
Figure 12: RESET ENABLE and RESET MEMORY Command	38
Figure 13: READ ID and MULTIPLE I/O READ ID Commands	39
Figure 14: READ SERIAL FLASH DISCOVERY PARAMETER Command – 5Ah	40
Figure 15: READ – 03h/13h ³	43
Figure 16: FAST READ – 0Bh/0Ch ³	43
Figure 17: DUAL OUTPUT FAST READ – 3Bh/3Ch ³	44
Figure 18: DUAL INPUT/OUTPUT FAST READ – BBh/BCh ³	44
Figure 19: QUAD OUTPUT FAST READ – 6Bh/6Ch ³	45
Figure 20: QUAD INPUT/OUTPUT FAST READ – EBh/ECh ³	45
Figure 21: QUAD INPUT/OUTPUT WORD READ – E7h ³	46
Figure 22: DTR FAST READ – 0Dh/E0h ³	47
Figure 23: DTR DUAL OUTPUT FAST READ – 3Dh ³	47
Figure 24: DTR DUAL INPUT/OUTPUT FAST READ – BDh ³	48
Figure 25: DTR QUAD OUTPUT FAST READ – 6Dh ³	49
Figure 26: DTR QUAD INPUT/OUTPUT FAST READ – EDh ³	49
Figure 27: WRITE ENABLE and WRITE DISABLE Timing	50
Figure 28: READ REGISTER Timing	51
Figure 29: WRITE REGISTER Timing	54
Figure 30: CLEAR FLAG STATUS REGISTER Timing	55
Figure 31: PAGE PROGRAM Command	57
Figure 32: DUAL INPUT FAST PROGRAM Command	58
Figure 33: EXTENDED DUAL INPUT FAST PROGRAM Command	58
Figure 34: QUAD INPUT FAST PROGRAM Command	59
Figure 35: EXTENDED QUAD INPUT FAST PROGRAM Command	59
Figure 36: SUBSECTOR , SECTOR ERASE and DIE ERASE Timing	61
Figure 37: PROGRAM/ERASE SUSPEND or RESUME Timing	63
Figure 38: READ OTP Command	64
Figure 39: PROGRAM OTP Command	65
Figure 40: XIP Mode Directly After Power-On	70
Figure 41: Power-Up Timing	73
Figure 42: AC Timing Input/Output Reference Levels	77
Figure 43: Reset AC Timing During PROGRAM or ERASE Cycle	83
Figure 44: Reset Enable and Reset Memory Timing	83
Figure 45: Serial Input Timing	83
Figure 46: Write Protect Setup and Hold During WRITE STATUS REGISTER Operation (SRWD = 1)	84
Figure 47: Hold Timing	84
Figure 48: Output Timing	84

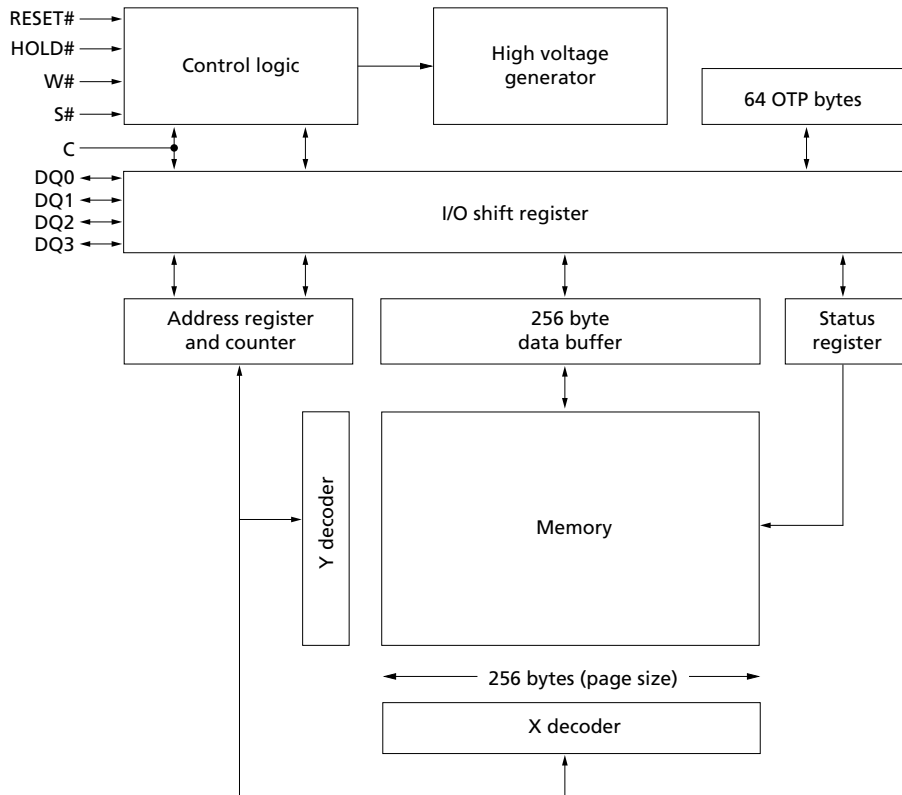
List of Tables

Table 1: Signal Descriptions	11
Table 2: Memory Map	15
Table 3: Status Register	16
Table 4: Protected Area	17
Table 5: Flag Status Register	18
Table 6: Extended Address Register	19
Table 7: Nonvolatile Configuration Register	21
Table 8: Volatile Configuration Register	23
Table 9: Sequence of Bytes During Wrap	23
Table 10: Clock Frequencies – STR (in MHz)	24
Table 11: Clock Frequencies – DTR (in MHz)	25
Table 12: Enhanced Volatile Configuration Register	26
Table 13: Sector Protection Register	28
Table 14: Global Freeze Bit	28
Table 15: Nonvolatile and Volatile Lock Bits	29
Table 16: Volatile Lock Bit Register	29
Table 17: Device ID Data	30
Table 18: Extended Device ID Data, First Byte	30
Table 19: Command Set	32
Table 20: RESET ENABLE and RESET MEMORY Operations	38
Table 21: READ ID and MULTIPLE I/O READ ID Operations	39
Table 22: READ MEMORY Operations	41
Table 23: 4-BYTE READ MEMORY Operations	42
Table 24: WRITE ENABLE/DISABLE Operations	50
Table 25: READ REGISTER Operations	51
Table 26: WRITE REGISTER Operations	53
Table 27: CLEAR FLAG STATUS REGISTER Operation	55
Table 28: PROGRAM Operations	56
Table 29: 4-BYTE PROGRAM Operations	57
Table 30: ERASE Operations	60
Table 31: SUSPEND/RESUME Operations	62
Table 32: OTP Control Byte (Byte 64)	65
Table 33: ENTER or EXIT 4-BYTE ADDRESS MODE Operations	66
Table 34: ENTER and RESET QUAD PROTOCOL Operations	66
Table 35: CRC Command Sequence on a Range	68
Table 36: Operations Allowed/Disallowed During Device States	69
Table 37: XIP Confirmation Bit	71
Table 38: Effects of Running XIP in Different Protocols	71
Table 39: Power-Up Timing and V_{WI} Threshold	73
Table 40: Absolute Ratings	76
Table 41: Operating Conditions	76
Table 42: Input/Output Capacitance	76
Table 43: AC Timing Input/Output Conditions	77
Table 44: DC Current Characteristics and Operating Conditions	78
Table 45: DC Voltage Characteristics and Operating Conditions	78
Table 46: AC Characteristics and Operating Conditions	80
Table 47: AC RESET Conditions	82
Table 48: Program/Erase Specifications	85

Device Description

The MT25Q is a high-performance multiple input/output serial Flash memory device. It features a high-speed SPI-compatible bus interface, execute-in-place (XIP) functionality, advanced write protection mechanisms, and extended address access. Innovative, high-performance, dual and quad input/output commands enable double or quadruple the transfer bandwidth for READ and PROGRAM operations.

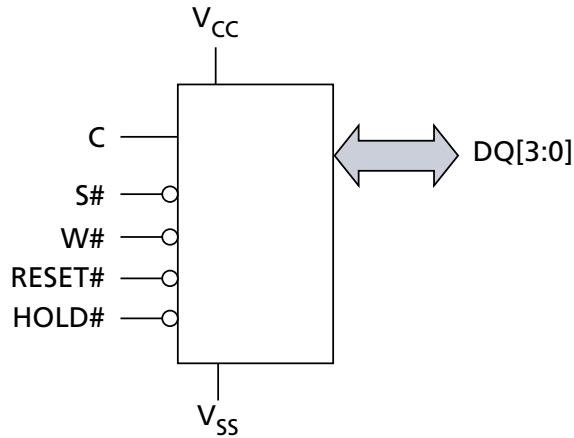
Figure 2: Block Diagram



Note: 1. Each page of memory can be individually programmed, but the device is not page-erasable.

Device Logic Diagram

Figure 3: Logic Diagram



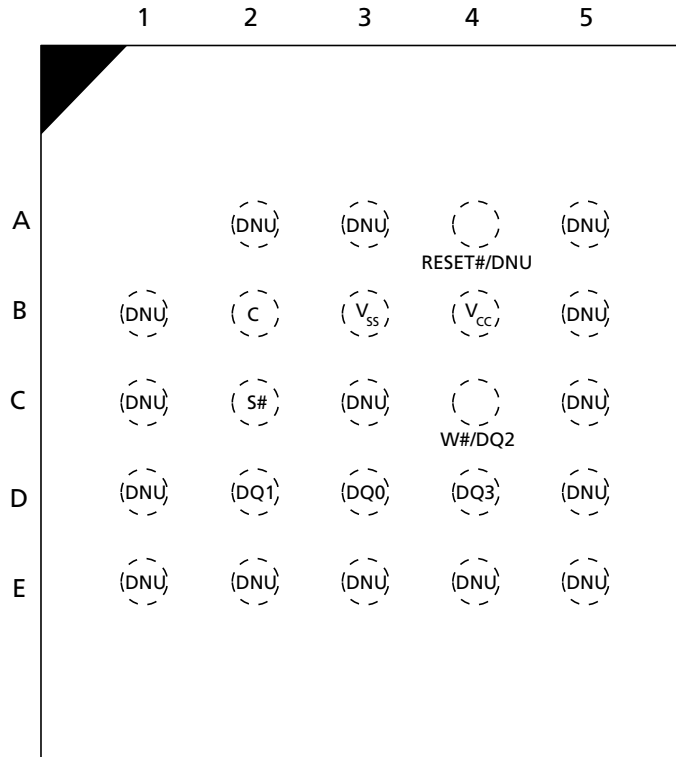
- Notes:
1. Depending on the selected device (see Part Numbering Ordering Information), DQ3 = DQ3/RESET# or DQ3/HOLD#.
 2. A separate RESET pin is available on dedicated part numbers (see Part Numbering Ordering Information).

Advanced Security Protection

The device offers an advanced security protection scheme where each sector can be independently locked, by either volatile or nonvolatile locking features. The nonvolatile locking configuration can also be locked, as well password-protected. See Block Protection Settings and Sector and Password Protection for more details.

Signal Assignments – Package Code: 12

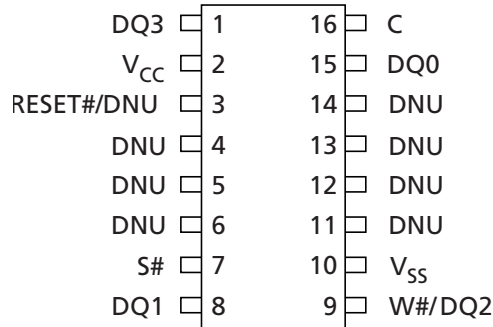
Figure 4: 24-Ball T-BGA, 5 x 5 (Balls Down)



- Notes:
1. RESET# or HOLD# signals can share Ball D4 with DQ3, depending on the selected device (see Part Numbering Ordering Information). When using single and dual I/O commands on these parts, DQ3 must be driven high by the host, or an external pull-up resistor must be placed on the PCB, in order to avoid allowing the HOLD# or RESET# input to float.
 2. Ball A4 = RESET# or DNU, depending on the part number. This signal has an internal pull-up resistor and may be left unconnected if not used.

Signal Assignments – Package Code: SF

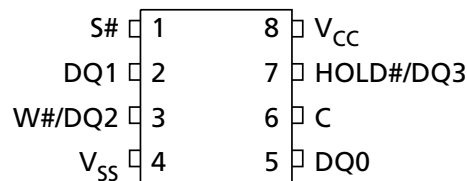
Figure 5: 16-Pin, Plastic Small Outline – SO16 (Top View)



- Notes:
1. RESET# or HOLD# signals can share Pin 1 with DQ3, depending on the selected device (see Part Numbering Ordering Information). When using single and dual I/O commands on these parts, DQ3 must be driven high by the host, or an external pull-up resistor must be placed on the PCB, in order to avoid allowing the HOLD# or RESET# input to float.
 2. Pin 3 = RESET# or DNU, depending on the part number. This signal has an internal pull-up resistor and may be left unconnected if not used.

Signal Assignments – Package Code: W9

Figure 6: 8-Pin, W-PDFN (Top View)



- Notes:
1. RESET# or HOLD# signals can share Pin 7 with DQ3, depending on the selected device (see Part Numbering Ordering Information). When using single and dual I/O commands on these parts, DQ3 must be driven high by the host, or an external pull-up resistor must be placed on the PCB, in order to avoid allowing the HOLD# or RESET# input to float.
 2. On the underside of the W-PDFN package, there is an exposed central pad that is pulled internally to V_{SS}. It can be left floating or can be connected to V_{SS}. It must not be connected to any other voltage or signal line on the PCB.

Signal Descriptions

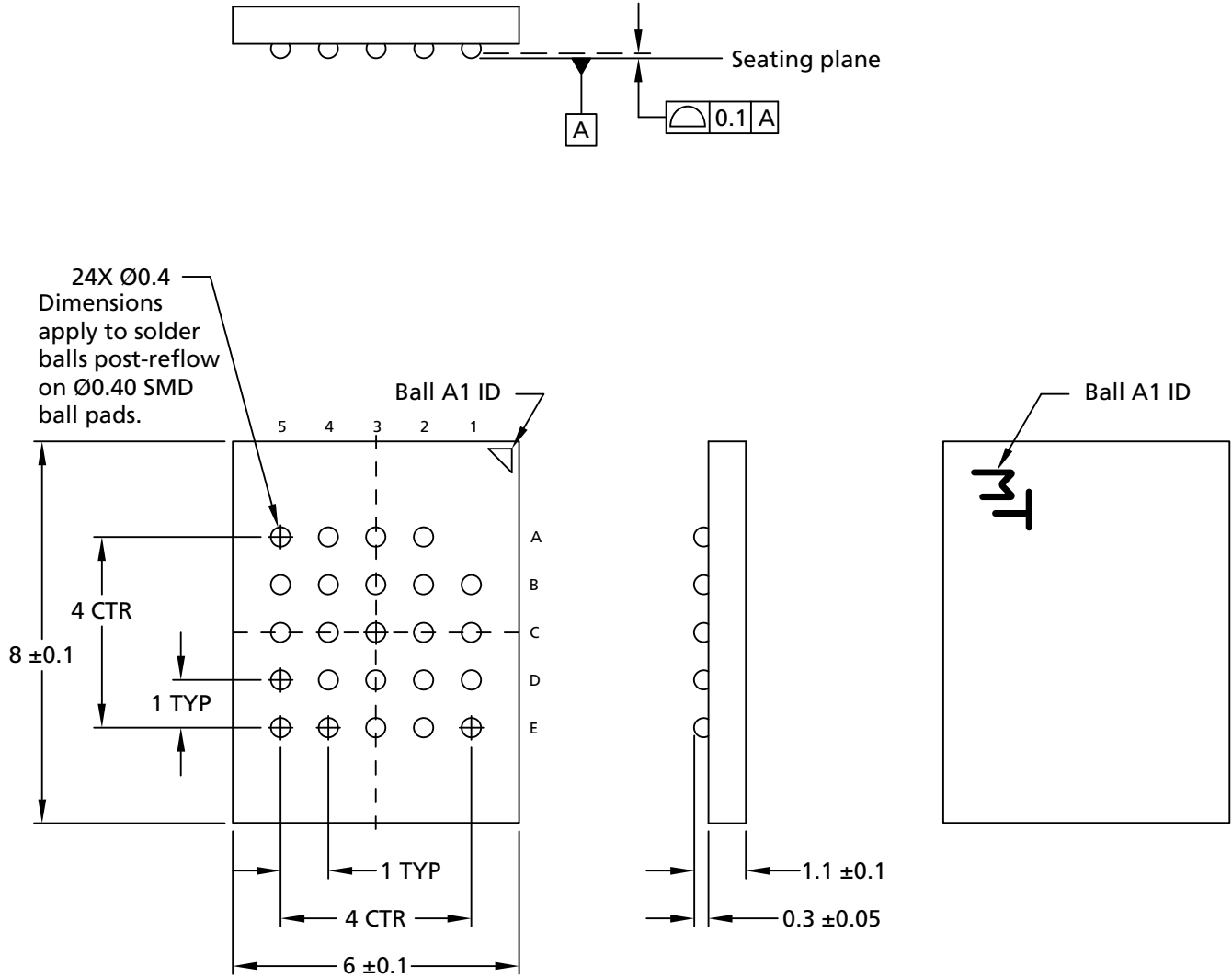
The signal description table below is a comprehensive list of signals for the MT25Q family devices. All signals listed may not be supported on this device. See Signal Assignments for information specific to this device.

Table 1: Signal Descriptions

Symbol	Type	Description
S#	Input	<p>Chip select: When S# is driven HIGH, the device will enter standby mode, unless an internal PROGRAM, ERASE, or WRITE STATUS REGISTER cycle is in progress. All other input pins are ignored and the output pins are tri-stated. On parts with the pin configuration offering a dedicated RESET# pin, however, the RESET# input pin remains active even when S# is HIGH.</p> <p>Driving S# LOW enables the device, placing it in the active mode.</p> <p>After power-up, a falling edge on S# is required prior to the start of any command.</p>
C	Input	<p>Clock: Provides the timing of the serial interface. Command inputs are latched on the rising edge of the clock. In STR commands or protocol, address and data inputs are latched on the rising edge of the clock, while data is output on the falling edge of the clock. In DTR commands or protocol, address and data inputs are latched on both edges of the clock, and data is output on both edges of the clock.</p>
RESET#	Input	<p>RESET#: When RESET# is driven LOW, the device is reset and the outputs are tri-stated. If RESET# is driven LOW while an internal WRITE, PROGRAM, or ERASE operation is in progress, data may be lost. The RESET# functionality can be disabled using bit 4 of the nonvolatile configuration register or bit 4 of the enhanced volatile configuration register.</p> <p>For pin configurations that share the DQ3 pin with RESET#, the RESET# functionality is disabled in QIO-SPI mode.</p>
HOLD#	Input	<p>HOLD: Pauses serial communications with the device without deselecting or resetting the device. Outputs are tri-stated and inputs are ignored. The HOLD# functionality can be disabled using bit 4 of the nonvolatile configuration register or bit 4 of the enhanced volatile configuration register.</p> <p>For pin configurations that share the DQ3 pin with HOLD#, the HOLD# functionality is disabled in QIO-SPI mode or when DTR operation is enabled.</p>
W#	Input	<p>Write protect: When LOW, the blocks defined by the block protection bits BP[3:0] are protected against PROGRAM or ERASE operations. Status register bit 7 should be set to 1 to enable write protection.</p>
DQ[3:0]	I/O	<p>Serial I/O: The bidirectional DQ signals transfer address, data, and command information.</p> <p>When using legacy (x1) SPI commands in extended I/O protocol (XIO-SPI), DQ0 is an input and DQ1 is an output. DQ[3:2] are not used.</p> <p>When using dual commands in XIO-SPI or when using DIO-SPI, DQ[1:0] are I/O. DQ[3:2] are not used.</p> <p>When using quad commands in XIO-SPI or when using QIO-SPI, DQ[3:0] are I/O.</p>
V _{CC}	Supply	Core and I/O power supply.
V _{SS}	Supply	Core and I/O ground connection.
DNU	–	Do not use. Must be left floating.
NC	–	No connect. Not internally connected.

Package Dimensions – Package Code: 12

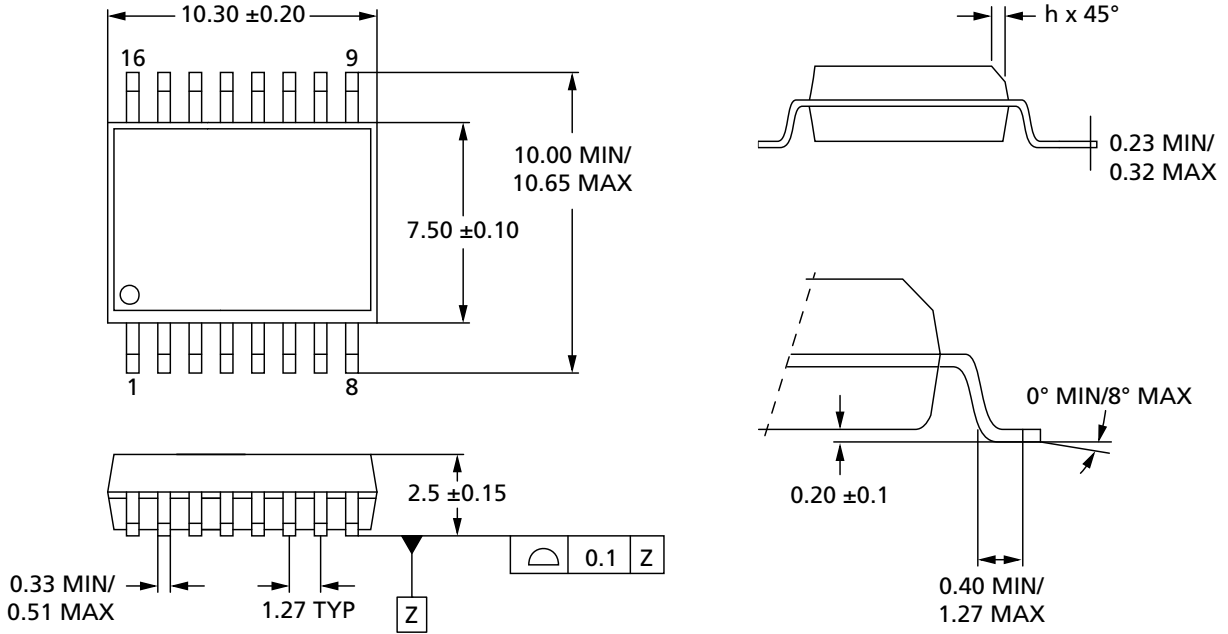
Figure 7: 24-Ball T-PBGA (5 x 5 ball grid array) – 6mm x 8mm



- Notes: 1. All dimensions are in millimeters.
2. See Part Number Ordering Information for complete package names and details.

Package Dimensions – Package Code: SF

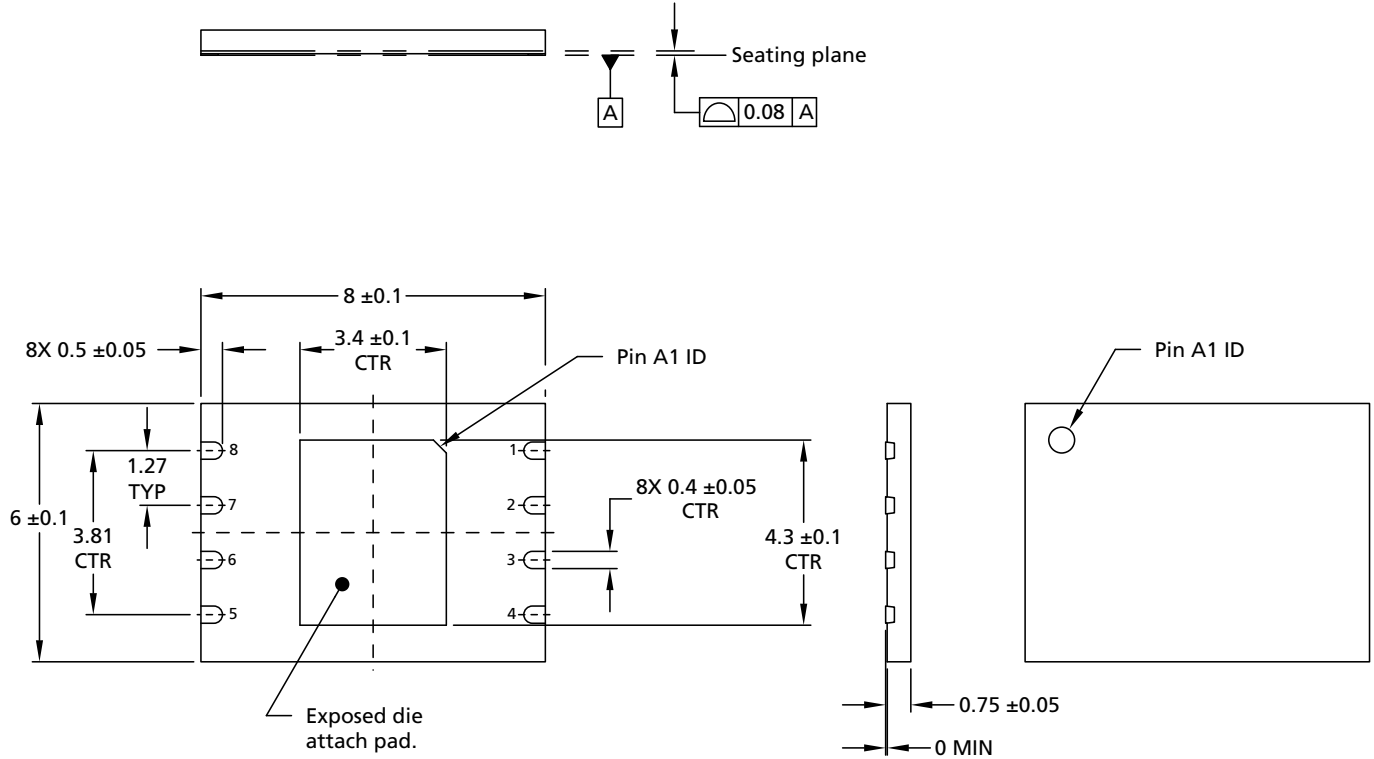
Figure 8: 16-Pin SOP2 – 300 mils Body Width



- Notes: 1. All dimensions are in millimeters.
2. See Part Number Ordering Information for complete package names and details.

Package Dimensions – Package Code: W9

Figure 9: W-PDFN-8 (MLP8) – 8mm x 6mm



- Notes: 1. All dimensions are in millimeters.
 2. See Part Number Ordering Information for complete package names and details.



Memory Map – 1Gb Density

Table 2: Memory Map

Sector	Subsector (32KB)	Subsector (4KB)	Address Range	
			Start	End
2047	4095	32767	07FF F000h	07FF FFFFh
		⋮	⋮	⋮
		32760	07FF 8000h	07FF 8FFFh
	4094	32759	07FF 7000h	07FF 7FFFh
		⋮	⋮	⋮
		32752	07FF 0000h	07FF 0FFFh
⋮	⋮	⋮	⋮	⋮
1023	2047	16383	03FF F000h	03FF FFFFh
		⋮	⋮	⋮
		16376	03FF 8000h	03FF 8FFFh
	2046	16375	03FF 7000h	03FF 7FFFh
		⋮	⋮	⋮
		16368	03FF 0000h	03FF 0FFFh
⋮	⋮	⋮	⋮	⋮
511	1023	8191	01FF F000h	01FF FFFFh
		⋮	⋮	⋮
		8184	01FF 8000h	01FF 8FFFh
	1022	8183	01FF 7000h	01FF 7FFFh
		⋮	⋮	⋮
		8176	01FF 0000h	01FF 0FFFh
⋮	⋮	⋮	⋮	⋮
0	1	15	0000 F000h	0000 FFFFh
		⋮	⋮	⋮
		8	0000 8000h	0000 8FFFh
	0	7	0000 7000h	0000 7FFFh
		⋮	⋮	⋮
		0	0000 0000h	0000 0FFFh

Note: 1. See Part Number Ordering Information, Sector Size – Part Numbers table for options.

Status Register

Status register bits can be read from or written to using READ STATUS REGISTER or WRITE STATUS REGISTER commands, respectively. When the status register enable/disable bit (bit 7) is set to 1 and W# is driven LOW, the status register nonvolatile bits become read-only and the WRITE STATUS REGISTER operation will not execute. The only way to exit this hardware-protected mode is to drive W# HIGH.

Table 3: Status Register

Bit	Name	Settings	Description	Notes
7	Status register write enable/disable	0 = Enabled 1 = Disabled (default)	Nonvolatile control bit: Used with W# to enable or disable writing to the status register.	
5	Top/bottom	0 = Top 1 = Bottom (default)	Nonvolatile control bit: Determines whether the protected memory area defined by the block protect bits starts from the top or bottom of the memory array.	
6, 4:2	BP[3:0]	See Protected Area tables	Nonvolatile control bit: Defines memory to be software protected against PROGRAM or ERASE operations. When one or more block protect bits is set to 1, a designated memory area is protected from PROGRAM and ERASE operations.	1
1	Write enable latch	0 = Clear (default) 1 = Set	Volatile control bit: The device always powers up with this bit cleared to prevent inadvertent WRITE, PROGRAM, or ERASE operations. To enable these operations, the WRITE ENABLE operation must be executed first to set this bit.	
0	Write in progress	0 = Ready 1 = Busy	Status bit: Indicates if one of the following command cycles is in progress: WRITE STATUS REGISTER WRITE NONVOLATILE CONFIGURATION REGISTER PROGRAM ERASE	2

- Notes:
1. The DIE ERASE command is executed only if all bits = 0.
 2. Status register bit 0 is the inverse of flag status register bit 7.



Block Protection Settings

Table 4: Protected Area

Status Register Content					Protected Area (Sectors)	Unprotected Area (Sectors)
Top/ Bottom	BP3	BP2	BP1	BP0		
0	0	0	0	0	None	All
0	0	0	0	1	2047	2046:0
0	0	0	1	0	2047:2046	2045:0
0	0	0	1	1	2047:2044	2043:0
0	0	1	0	0	2047:2040	2039:0
0	0	1	0	1	2047:2032	2031:0
0	0	1	1	0	2047:2016	2015:0
0	0	1	1	1	2047:1984	1983:0
0	1	0	0	0	2047:1920	1919:0
0	1	0	0	1	2047:1792	1791:0
0	1	0	1	0	2047:1536	1535:0
0	1	0	1	1	2047:1024	1023:0
0	1	1	0	0	All	None
0	1	1	0	1	All	None
0	1	1	1	0	All	None
0	1	1	1	1	All	None
1	0	0	0	0	None	All
1	0	0	0	1	Sector 0	2047:1
1	0	0	1	0	1:0	2047:2
1	0	0	1	1	3:0	2047:4
1	0	1	0	0	7:0	2047:8
1	0	1	0	1	15:0	2047:16
1	0	1	1	0	31:0	2047:32
1	0	1	1	1	63:0	2047:64
1	1	0	0	0	127:0	2047:128
1	1	0	0	1	255:0	2047:256
1	1	0	1	0	511:0	2047:512
1	1	0	1	1	1023:0	2047:1024
1	1	1	0	0	All	None
1	1	1	0	1	All	None
1	1	1	1	0	All	None
1	1	1	1	1	All	None

Flag Status Register

Flag status register bits are read by using READ FLAG STATUS REGISTER command. All bits are volatile and are reset to zero on power up.

Status bits are set and reset automatically by the internal controller. Error bits must be cleared through the CLEAR STATUS REGISTER command.

Table 5: Flag Status Register

Bit	Name	Settings	Description
7	Program or erase controller	0 = Busy 1 = Ready	Status bit: Indicates whether one of the following command cycles is in progress: WRITE STATUS REGISTER, WRITE NONVOLATILE CONFIGURATION REGISTER, PROGRAM, or ERASE.
6	Erase suspend	0 = Clear 1 = Suspend	Status bit: Indicates whether an ERASE operation has been or is going to be suspended.
5	Erase	0 = Clear 1 = Failure or protection error	Error bit: Indicates whether an ERASE operation has succeeded or failed.
4	Program	0 = Clear 1 = Failure or protection error	Error bit: Indicates whether a PROGRAM operation has succeeded or failed. It indicates, also, whether a CRC check has succeeded or failed.
3	Reserved	0	Reserved
2	Program suspend	0 = Clear 1 = Suspend	Status bit: Indicates whether a PROGRAM operation has been or is going to be suspended.
1	Protection	0 = Clear 1 = Failure or protection error	Error bit: Indicates whether an ERASE or PROGRAM operation has attempted to modify the protected array sector, or whether a PROGRAM operation has attempted to access the locked OTP space.
0	Addressing	0 = 3-byte addressing 1 = 4-byte addressing	Status bit: Indicates whether 3-byte or 4-byte address mode is enabled.

Extended Address Register

The 3-byte address mode can only access 128Mb of memory. To access the full device in 3-byte address mode, the device includes an extended address register that indirectly provides a fourth address byte A[31:24]. The extended address register bits [2:0] operate as memory address bit A[26:24] to select one of the eight 128Mb segments of the memory array.

If 4-byte addressing is enabled, the extended address register settings are ignored.

Table 6: Extended Address Register

Bit	Name	Settings	Description
7:3	A[31:25]	000000	Reserved
2:0	A[26:24]	111 = Highest 128Mb segment 110 = Seventh 128Mb segment 101 = Sixth 128Mb segment 100 = Fifth 128Mb segment 011 = Fourth 128Mb segment 010 = Third 128Mb segment 001 = Second 128Mb segment 000 = Lowest 128Mb segment	Enables specified 128Mb memory segment. The default setting (lowest) can be changed to the highest 128Mb segment using bit 1 of the nonvolatile configuration register.

The PROGRAM and ERASE operations act upon the 128Mb segment selected in the extended address register. The DIE ERASE operation erases the selected die.

The READ operation begins reading in the selected 128Mb segment, but is not bound by it.

In a continuous READ, when the last byte of the segment is read, the next byte output is the first byte of the next segment. The operation wraps to 0000000h; therefore, a download of the whole array is possible with one READ operation.

The value of the extended address register does not change when a READ operation crosses the selected 128Mb boundary.

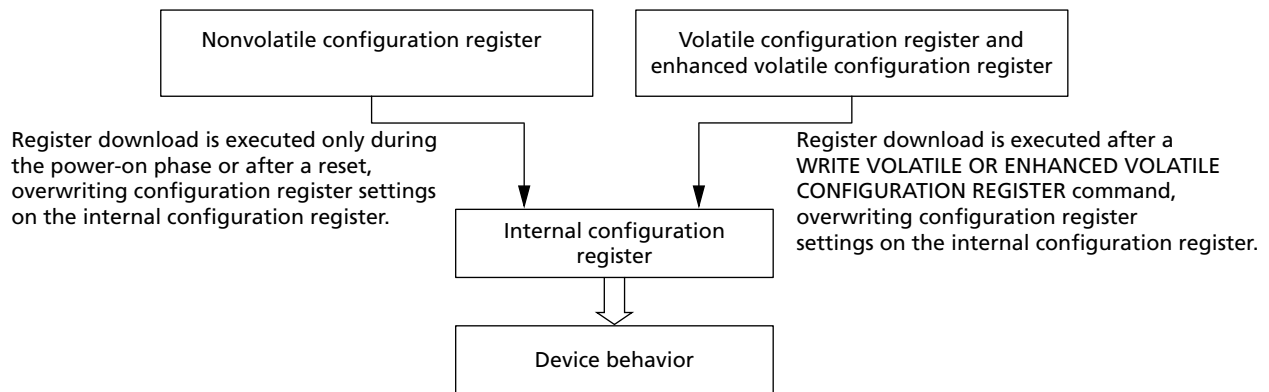
Internal Configuration Register

The memory configuration is set by an internal configuration register that is not directly accessible to users.

The user can change the default configuration at power up by using the WRITE NON-VOLATILE CONFIGURATION REGISTER. Information from the nonvolatile configuration register overwrites the internal configuration register during power on or after a reset.

The user can change the configuration during operation by using the WRITE VOLATILE CONFIGURATION REGISTER or the WRITE ENHANCED VOLATILE CONFIGURATION REGISTER commands. Information from the volatile configuration registers overwrite the internal configuration register immediately after the WRITE command completes.

Figure 10: Internal Configuration Register



Nonvolatile Configuration Register

This register is read from and written to using the READ NONVOLATILE CONFIGURATION REGISTER and the WRITE NONVOLATILE CONFIGURATION REGISTER commands, respectively. A register download is executed during power-on or after reset, overwriting the internal configuration register settings that determine device behavior.

Table 7: Nonvolatile Configuration Register

Bit	Name	Settings	Description	Notes
15:12	Number of dummy clock cycles	0000 = Default 0001 = 1 0010 = 2 : 1101 = 13 1110 = 14 1111 = Default	Sets the number of dummy clock cycles subsequent to all FAST READ commands (See the Command Set Table for default setting values).	1
11:9	XIP mode at power-on reset	000 = XIP: Fast read 001 = XIP: Dual output fast read 010 = XIP: Dual I/O fast read 011 = XIP: Quad output fast read 100 = XIP: Quad I/O fast read 101 = Reserved 110 = Reserved 111 = Disabled (Default)	Enables the device to operate in the selected XIP mode immediately after power-on reset.	
8:6	Output driver strength	000 = Reserved 001 = 90 Ohms 010 = Reserved 011 = 45 Ohms 100 = Reserved 101 = 20 Ohms 110 = Reserved 111 = 30 Ohms (Default)	Optimizes the impedance at $V_{CC}/2$ output voltage.	
5	Double transfer rate protocol	0 = Enabled 1 = Disabled (Default)	Set DTR protocol as current one. Once enabled, all commands will work in DTR.	
4	Reset/hold	0 = Disabled 1 = Enabled (Default)	Enables or disables HOLD# or RESET# on DQ3.	
3	Quad I/O protocol	0 = Enabled 1 = Disabled (Default)	Enables or disables quad I/O command input (4-4-4 mode).	2
2	Dual I/O protocol	0 = Enabled 1 = Disabled (Default)	Enables or disables dual I/O command input (2-2-2 mode).	2
1	128Mb segment select	0 = Highest 128Mb segment 1 = Lowest 128Mb segment (Default)	Selects the power-on default 128Mb segment for 3-byte address operations. See also the extended address register.	

Table 7: Nonvolatile Configuration Register (Continued)

Bit	Name	Settings	Description	Notes
0	Number of address bytes during command entry	0 = Enable 4-byte address mode 1 = Enable 3-byte address mode (Default)	Defines the number of address bytes for a command.	

- Notes:
1. The number of cycles must be set to accord with the clock frequency, which varies by the type of FAST READ command (See Supported Clock Frequencies table). Insufficient dummy clock cycles for the operating frequency causes the memory to read incorrect data.
 2. When bits 2 and 3 are both set to 0, the device operates in quad I/O protocol.

Volatile Configuration Register

This register is read from and written to by the READ VOLATILE CONFIGURATION REGISTER and the WRITE VOLATILE CONFIGURATION REGISTER commands, respectively. A register download is executed after these commands, overwriting the internal configuration register settings that determine device memory behavior.

Table 8: Volatile Configuration Register

Bit	Name	Settings	Description	Notes
7:4	Number of dummy clock cycles	0000 = Default 0001 = 1 0010 = 2 : 1101 = 13 1110 = 14 1111 = Default	Sets the number of dummy clock cycles subsequent to all FAST READ commands (See the Command Set Table for default setting values).	1
3	XIP	0 = Enable 1 = Disable (default)	Enables or disables XIP.	
2	Reserved	0	0b = Fixed value.	
1:0	Wrap	00 = 16-byte boundary aligned	16-byte wrap: Output data wraps within an aligned 16-byte boundary starting from the 3-byte address issued after the command code.	2
		01 = 32-byte boundary aligned	32-byte wrap: Output data wraps within an aligned 32-byte boundary starting from the 3-byte address issued after the command code.	
		10 = 64-byte boundary aligned	64-byte wrap: Output data wraps within an aligned 64-byte boundary starting from the 3-byte address issued after the command code.	
		11 = Continuous (default)	Continuously sequences addresses through the entire array.	

- Notes:
1. The number of cycles must be set according to and sufficient for the clock frequency, which varies by the type of FAST READ command, as shown in the Supported Clock Frequencies table. An insufficient number of dummy clock cycles for the operating frequency causes the memory to read incorrect data.
 2. See the Sequence of Bytes During Wrap table.

Table 9: Sequence of Bytes During Wrap

Starting Address	16-Byte Wrap	32-Byte Wrap	64-Byte Wrap
0	0-1-2- ... -15-0-1- ..	0-1-2- ... -31-0-1- ..	0-1-2- ... -63-0-1- ..
1	1-2- ... -15-0-1-2- ..	1-2- ... -31-0-1-2- ..	1-2- ... -63-0-1-2- ..
....
15	15-0-1-2-3- ... -15-0-1- ..	15-16-17- ... -31-0-1- ..	15-16-17- ... -63-0-1- ..
....
31	-	31-0-1-2-3- ... -31-0-1- ..	31-32-33- ... -63-0-1- ..
....
63	-	-	63-0-1- ... -63-0-1- ..

Supported Clock Frequencies

Table 10: Clock Frequencies – STR (in MHz)

Notes apply to entire table

Number of Dummy Clock Cycles	FAST READ	DUAL OUTPUT FAST READ	DUAL I/O FAST READ	QUAD OUTPUT FAST READ	QUAD I/O FAST READ
1	94	79	60	44	39
2	112	97	77	61	48
3	129	106	86	78	58
4	133	115	97	97	69
5	133	125	106	106	78
6	133	133	115	115	86
7	133	133	125	125	97
8	133	133	133	133	106
9	133	133	133	133	115
10	133	133	133	133	125
11 : 14	133	133	133	133	133

- Notes:
1. Values are guaranteed by characterization and not 100% tested in production.
 2. A tuning data pattern (TDP) capability provides applications with data patterns for adjusting the data latching point at the host end when the clock frequency is set higher than 133 MHz in STR mode and higher than 66 MHz in double transfer rate (DTR) mode. For additional details, refer to TN-25-07: Tuning Data Pattern for MT25Q and MT25T Devices.

Table 11: Clock Frequencies – DTR (in MHz)

Notes apply to entire table

Number of Dummy Clock Cycles	FAST READ	DUAL OUTPUT FAST READ	DUAL I/O FAST READ	QUAD OUTPUT FAST READ	QUAD I/O FAST READ
1	59	45	40	26	20
2	73	59	49	40	30
3	82	68	59	59	39
4	90	76	65	65	49
5	90	83	75	75	58
6	90	90	83	83	68
7	90	90	90	90	78
8	90	90	90	90	85
9	90	90	90	90	90
10 : 14	90	90	90	90	90

- Notes:
1. Values are guaranteed by characterization and not 100% tested in production.
 2. A tuning data pattern (TDP) capability provides applications with data patterns for adjusting the data latching point at the host end when the clock frequency is set higher than 133 MHz in STR mode and higher than 66 MHz in double transfer rate (DTR) mode. For additional details, refer to TN-25-07: Tuning Data Pattern for MT25Q and MT25T Devices.